SHARP

PC410S0NIP0F Series

High Speed 10Mb/s, High CMR Mini-flat Package *OPIC Photocoupler



Description

PC410S0NIP0F Series contains a LED optically coupled to an OPIC.

It is packaged in a 8 pin mini-flat.

Input-output isolation voltage(rms) is 3.75 kV.

High speed response (TYP. 10Mb/s) and CMR is MIN. 10kV/ $\mu s.$

Features

- 1.8 pin Mini-flat package
- 2. Double transfer mold package (Ideal for Flow Soldering)
- High noise immunity due to high instantaneous common mode rejection voltage (CM_H : MIN. 10kV/μs, CM_L : MIN. –10kV/μs)
- 4. High speed response (t_{PHL} : TYP. 48ns, t_{PLH} : TYP. 50ns)
- 5. Isolation voltage between input and output ($V_{iso(rms)}$: 3.75kV)
- 6. Lead-free and RoHS driective compliant

■ Agency approvals/Compliance

- 1. Recognized by UL1577 (Double protection isolation), file No. E64380 (as model No. **PC410S**)
- 2. Approved by VDE, DIN EN60747-5-2^(*) (as an option), file No. 40009162 (as model No. **PC410S**)
- 3. Package resin : UL flammability grade (94V-0))

(*) DIN EN60747-5-2 : successor standard of DIN VDE0884.

Applications

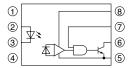
- 1. Programmable controller
- 2. Inverter

* "OPIC"(Optical IC) is a trademark of the SHARP Corporation. An OPIC consists of a light-detecting element and a signal-processing circuit integrated onto a single chip.

Notice The content of data sheet is subject to change without prior notice. In the absence of confirmation by device specification sheets, SHARP takes no responsibility for any defects that may occur in equipment using any SHARP devices shown in catalogs, data books, etc. Contact SHARP in order to obtain the latest device specification sheets before using any SHARP device.



Internal Connection Diagram



① N.C.^{*} ⑤ GND ② Anode ⑥ V₀ (Open collector) ③ Cathode ⑦ V_E (Enable) ④ N.C.^{*} ⑧ V_{CC}

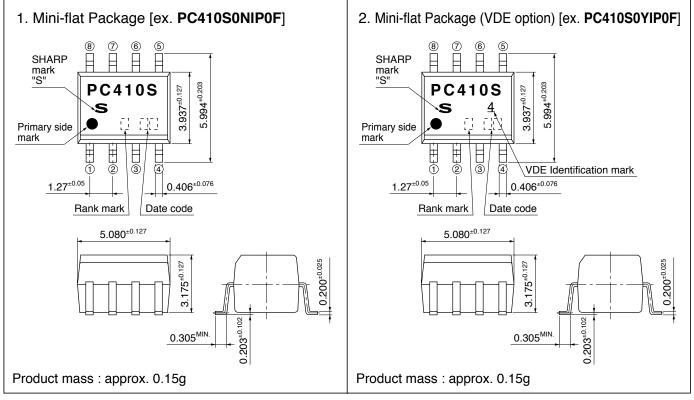
*As for N.C. pins (①, ④), external connection is not allowed.

Truth table

Input	Enable	Output	
Н	Н	L	
L	Н	Н	
Н	L	Н	L : Logic (0)
L	L	Н	H:Logic(1)

Outline Dimensions

(Unit : mm)



Plating material : Pd (Au flush)



Date code (2 digit)

	1st o	digit		2nd digit		
	Year of p	roduction		Month of production		
A.D.	Mark	Mark A.D. Mark Month		Month	Mark	
1990	А	2002	Р	January	1	
1991	В	2003	R	February	2	
1992	С	2004	S	March	3	
1993	D	2005	Т	April	4	
1994	Е	2006	U	May	5	
1995	F	2007	V	June	6	
1996	Н	2008	W	July	7	
1997	J	2009	Х	August	8	
1998	K	2010	А	September	9	
1999	L	2011	В	October	0	
2000	М	2012	С	November	N	
2001	N	:	:	December	D	

repeats in a 20 year cycle

Country of origin Japan

Rank mark

With or without.

■ Absolute Maximum Ratings

Abs	solute Maximum Ratings	5		$(T_a=T_{opr})$
	Parameter	Symbol	Rating	Unit
	*1 Forward current	$\begin{tabular}{ c c c c c } \hline Symbol & Rating \\ \hline I_F & 20 \\ \hline V_R & 5 \\ \hline P & 40 \\ \hline V_{CC} & 7 \\ \hline V_E & V_{CC} + 0.5 \\ \hline I_E & 5 \\ \hline tage & V_{OH} & 7 \\ \hline ent & I_{OL} & 50 \\ \hline \end{tabular}$	mA	
Input	Reverse voltage	V _R	5	V
	Power dissipation	Р	40	mW
	Supply voltage	V _{CC}	7	V
	Enable voltage	$V_{\rm E}$	V _{CC} +0.5	V
Output	Enable inpout current	$\begin{tabular}{ c c c c c c } \hline Symbol & Rating & Unit \\ \hline I_F & 20 & mA \\ \hline V_R & 5 & V \\ \hline P & 40 & mW \\ \hline V_{CC} & 7 & V \\ \hline V_E & V_{CC}+0.5 & V \\ \hline I_E & 5 & mA \\ \hline V_{OH} & 7 & V \\ \hline I_{OL} & 50 & mA \\ \hline tion & P_C & 85 & mW \\ \hline T_{opr} & -40 to +85 & ^{\circ}C \\ \hline T_{stg} & -55 to +125 & ^{\circ}C \\ \hline V_{iso(rms)} & 3.75 & kV \\ \hline \end{tabular}$	mA	
Output	High level output voltage		V	
	Low level output current		mA	
	*2 Output collector power dissipation	P _C	85	mW
Opera	ating temperature	T _{opr}	-40 to +85	°C
Stora	ge temperature	T _{stg}	-55 to +125	°C
*3 Isolation voltage		V _{iso(rms)}	3.75	kV
*4 Soldering temperature		T _{sol}	270	°C

Refer to Fig.4

Refer to Fig.5 40 to 60%RH, AC for 1minute, f=60Hz

For 10s

Electro-optical Characteristics

(Unless otherwise specified $T_a=-40$ to $85^{\circ}C$)

		Parameter	Symbol	Conc	lition	MIN.	TYP.*5	MAX.	Unit
	Forward voltage		V_{F}	$I_F=1$	0mA	1.3	-	1.8	v
Input	FC	of ward voltage	ν _F	T _a =25°C,	I _F =10mA	1.4	1.5	1.75	v
Inp	Re	everse current	I _R	T _a =25°C	, V _R =5V	-	-	10	μΑ
	Те	erminal capacitance	Ct	Ta=25°C, V	=0, f=1MHz	_	60	-	pF
	H	igh level output voltage	I _{OH}	$V_{CC}=V_{O}=5.5V, V_{E}=2V, I_{F}=250\mu A$		_	0.02	100	μΑ
t	Low level output voltage		V _{OL}	$V_{CC}=5.5V, V_{E}=2V, I_{F}=5mA, I_{OL}=13mA$		-	0.4	0.6	V
	H	igh level enable current	$I_{\rm EH}$	V _{CC} =5.5	-	-0.5	-1.6	mA	
itpu	L	ow level enable current	I_{EL}	V _{CC} =5.5V	$V_{\rm E}=0.5V$	_	-0.7	-1.6	mA
*6 Output		ah laval annulu annuat	т	V _{CC} =5.5V, V	$V_{\rm E}=V_{\rm CC}, I_{\rm F}=0$	-	5	-	mA
*	п	igh level supply current	I _{CCH}	V _{CC} =5.5V, V	$I_{\rm E}=0.5$ V, $I_{\rm F}=0$	-	5	10	mA
	L	ow level supply current	т	$V_{CC}=5.5V, V_{E}=V_{CC}, I_{F}=10mA$		_	7	-	mA
		Sw level supply current	I _{CCL}	$V_{CC}=5.5V, V_{E}=$	0.5V, I _F =10mA	-	5.5	13	mA
	"High→Low" input threshold current		I_{FHL}	$V_{CC}=5V, V_{E}=2V, V_{O}=0.6V, R_{L}=350\Omega$		-	2.5	5	mA
	Isolation resistance		R _{ISO}	$T_a=25^{\circ}C$, DC500V, 40 to 60%RH		5×10 ¹⁰	10 ¹¹	-	Ω
	Floating capacitance		$C_{\rm f}$	$T_a=25$ °C, V=0, f=1MHz		_	0.6	-	pF
		"High-Low" propagation delay time	t _{PHL}			25	48	75	ns
		"Low→High" propagation delay time	t _{PLH}	T _a =25°C, I _F =7.5mA, V _{CC} =5V, R _L =350W, C _L =15pF,		25	50	75	ns
stics		Rise time	t _r			_	20	-	ns
teris	ime	Fall time	t _f			-	10	-	ns
Irac	Response time	^{*7} Distortion of pulse width	$\Delta t_{\rm W}$		_	_	35	ns	
cha	bou	Propagation delay skew	t _{PSK}			_	-	40	ns
*6 Transfer characteristics	Res	"High→Low" enable propagation	t	т 25°С I 7	.5mA, V _{CC} =5V,		15	_	ns
rans		delay time	t _{EHL}	$R_{L}=350\Omega, C_{L}=$		-	15	-	115
*6T		"Low→High" enable propagation	t		L=0		10		ns
		delay time	t _{ELH}	V E.	L=0		10	_	115
	Instantaneous common mode rejection		CM_{H}	CM_{H} I _F =0, $V_{O(Min)}=2V$ T _a =25°C, $V_{CC}=5V$,	10	20		kV/μs	
		oltage (High level output)	CIVIH		$V_{CM}=1kV_{(P-P)},$, 10	20		κν/μs
		stantaneous common mode rejection	CML	I _F =5mA,	$V_{CM} = 1K V_{(P-P)},$ $R_L = 350\Omega$	-10	-20	_	kV/μs
	VC	oltage (Low level output)	C.,.T	V _{O(MAX)} =0.8V	10				

*5 All typical values at V_{CC}=5V, T_a=25^{\circ}C

*6 It shall connect a by-pass capacitor of 0.01 µF or more between V_{CC} (pin (18)) and GND (pin (15)) near the device, when it measures the transfer characteristics and the output side characteristics

*7 Distortion of pulse width $\Delta_{tw}\text{=}\mid t_{PHL}\text{-}t_{PLH}\mid$



■ Model Line-up

Doolsogo	Taping		
Package	1 500pcs/reel		
DIN EN60747-5-2		Approved	
Model No.	PC410S0NIP0F	PC410S0YIP0F	

Please contact a local SHARP sales representative to inquire about production status.



Fig.1 Test Circuit for Propagation Delay Time and Rise Time, Fall Time

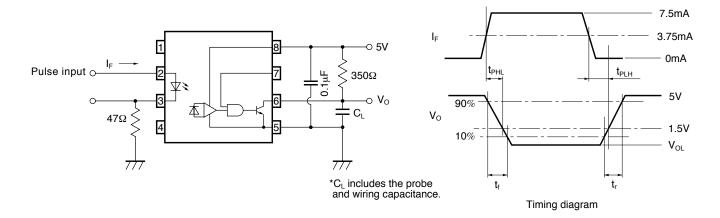
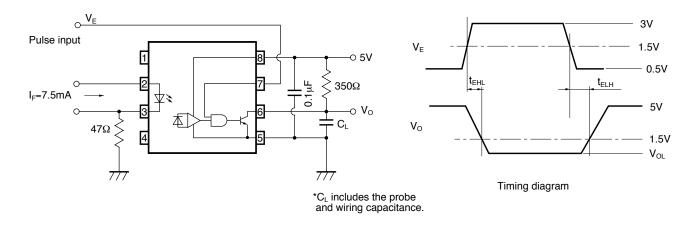


Fig.2 Test Circuit for Enable Propagation Delay Time





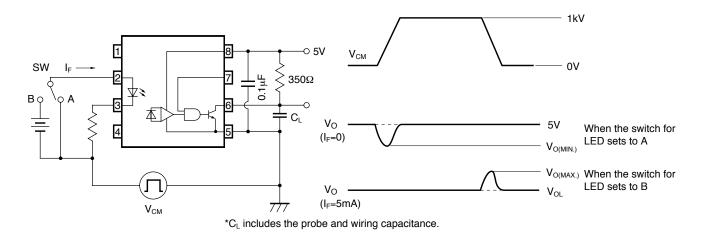


Fig.4 Forward Current vs. Ambient Temperature

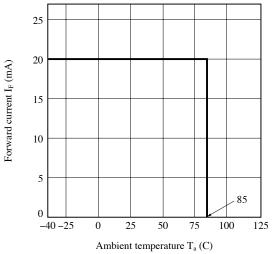
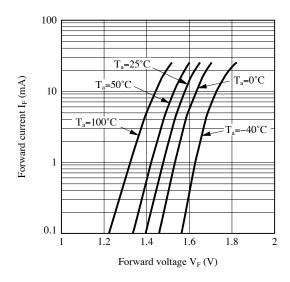


Fig.6 Forward Current vs. Forward Voltage





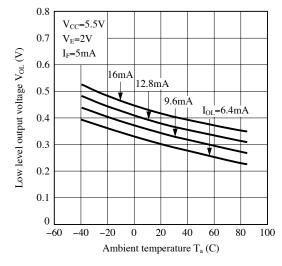


Fig.5 Output Collector Power Dissipation vs. Ambient Temperature

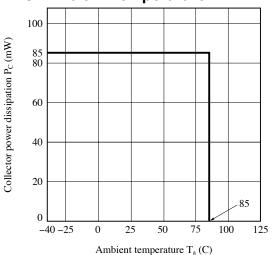


Fig.7 High Level Output Current vs. Ambient Temperature

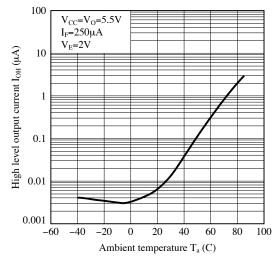
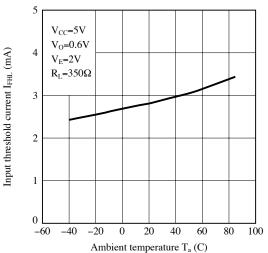
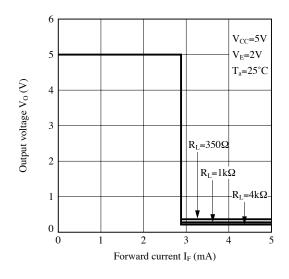


Fig.9 Input Threshold Current vs. Ambient Temperature

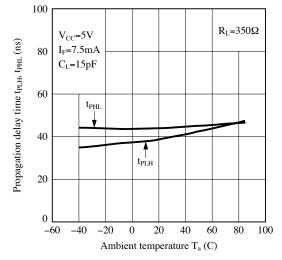


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Fig.10 Output Voltage vs. Forward Current









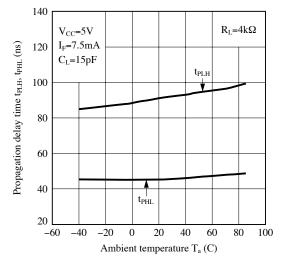


Fig.11 Propagation Delay Time vs. Forward Current

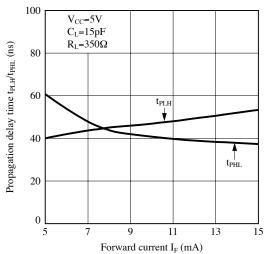


Fig.12-b Propagation Delay Time vs. Ambient Temperature

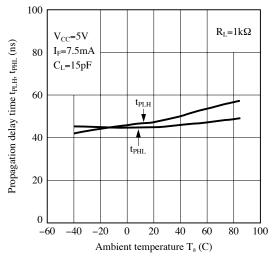


Fig.13 Response Time vs. Ambient Temperature

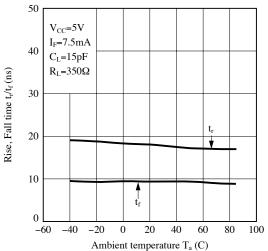
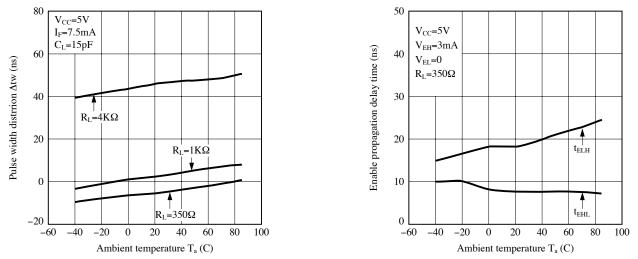




Fig.14 Distortion of Pulse width vs. Ambient Temperature



Remarks : Please be aware that all data in the graph are just for reference and anot for guarantee.

Fig.15 Erable Propagation Delay Time vs. Ambient Temperature

Design Considerations

• Recommended operating conditions

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Low level input current	I _{FL}	0	_	250	μΑ
High level input current	I _{FH}	8	_	15	mA
High level enable input voltage	V_{EH}	2	_	V _{CC}	V
Low level enable input voltage	V _{EL}	0	-	0.8	V
Supply voltage	V _{CC}	4.5	-	5.5	V
Fan out (TTL load)	N	_	-	5	-
Output pull-up resistor	R _L	330	_	4 000	Ω
Operating temperature	T _{opr}	_40	_	85	°C

Notes about static electricity

Transistor of detector side in bipolar configuration may be damaged by static electricity due to its minute design.

When handling these devices, general countermeasure against static electricity should be taken to avoid breakdown of devices or degradation of characteristics.

• Design guide

In order to stabilize power supply line, we should certainly recommend to connect a by-pass capacitor of 0.01μ F or more between V_{CC} and GND near the device.

In case that some sudden big noise caused by voltage variation is provided between primary and secondary terminals of photocoupler some current caused by it is floating capacitance may be generated and result in false operation since current may go through LED or current may change.

If the photocoupler may be used under the circumstances where noise will be generated we recommend to use the bypass capacitors at the both ends of LED.

The detector which is used in this device, has parasitic diode between each pins and GND.

There are cases that miss operation or destruction possibly may be occurred if electric potential of any pin becomes below GND level even for instant.

Therefore it shall be recommended to design the circuit that electric potential of any pin does not become below GND level.

As for N.C. pins (①, ④), external connection is not allowed.

This product is not designed against irradiation and incorporates non-coherent LED.

Degradation

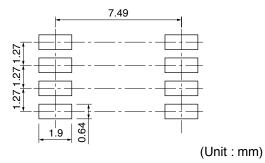
In general, the emission of the LED used in photocouplers will degrade over time.

In the case of long term operation, please take the general LED degradation (50% degradation over 5 years) into the design consideration.

Please decide the input current which become 2 times of MAX. I_{FHL} .



• Recommended foot print (reference)



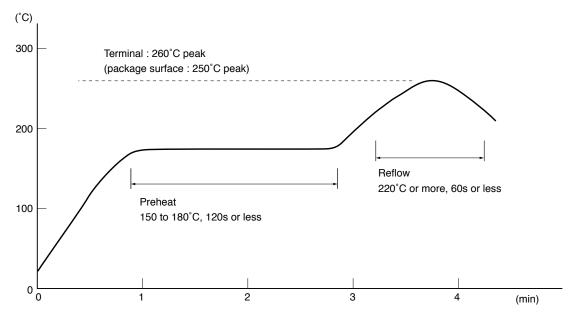


Manufacturing Guidelines

Soldering Method

Reflow Soldering:

Reflow soldering should follow the temperature profile shown below. Soldering should not exceed the curve of temperature profile and time. Please don't solder more than twice.



Flow Soldering :

Due to SHARP's double transfer mold construction submersion in flow solder bath is allowed under the below listed guidelines.

Flow soldering should be completed below 270°C and within 10s. Preheating is within the bounds of 100 to 150°C and 30 to 80s. Please don't solder more than twice.

Hand soldering

Hand soldering should be completed within 3s when the point of solder iron is below 400°C. Please don't solder more than twice.

Other notice

Please test the soldering method in actual condition and make sure the soldering works fine, since the impact on the junction between the device and PCB varies depending on the tooling and soldering conditions.



• Cleaning instructions

Solvent cleaning :

Solvent temperature should be 45°C or below. Immersion time should be 3 minutes or less.

Ultrasonic cleaning :

The impact on the device varies depending on the size of the cleaning bath, ultrasonic output, cleaning time, size of PCB and mounting method of the device.

Therefore, please make sure the device withstands the ultrasonic cleaning in actual conditions in advance of mass production.

Recommended solvent materials :

Ethyl alcohol, Methyl alcohol and Isopropyl alcohol.

In case the other type of solvent materials are intended to be used, please make sure they work fine in actual using conditions since some materials may erode the packaging resin.

• Presence of ODC

This product shall not contain the following materials. And they are not used in the production process for this product. Regulation substances : CFCs, Halon, Carbon tetrachloride, 1.1.1-Trichloroethane (Methylchloroform)

Specific brominated flame retardants such as the PBB and PBDE are not used in this product at all.

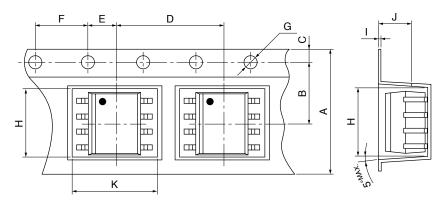
This product shall not contain the following materials banned in the RoHS Directive (2002/95/EC).
•Lead, Mercury, Cadmium, Hexavalent chromium, Polybrominated biphenyls (PBB), Polybrominated diphenyl ethers (PBDE).



• Tape and Reel package SMT Gullwing

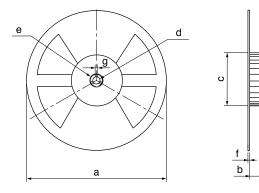
Package materials Carrier tape : PS Cover tape : PET (three layer system) Reel : PS

Carrier tape structure and Dimensions



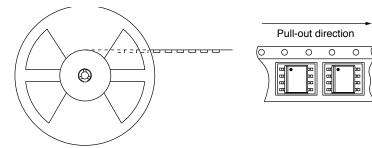
Dimensions List (Unit : mm)						
А	В	С	D	Е	F	G
$12.0^{\pm 0.3}$	5.50 ^{±0.05}	$1.75^{\pm 0.10}$	$8.0^{\pm0.1}$	$2.00^{\pm 0.05}$	$4.0^{\pm 0.1}$	φ1.55 ^{±0.05}
Н	Ι	J	K			
$5.4^{\pm 0.1}$	0.30 ^{±0.05}	$3.7^{\pm 0.1}$	6.3 ^{±0.1}			

Reel structure and Dimensions



Dimensio	ns List	(Unit : mm)			
а	b	с	d		
φ330	φ330 13.5 ^{±1.5}		\$\$13.0 ^{±0.2}		
e	f	g			
¢21.0 ^{±0.8}	2.0 ^{TYP.}	2.0 ^{±0.5}			

Direction of product insertion



[Packing : 1 500pcs/reel]

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- --- Personal computers
- --- Office automation equipment
- --- Telecommunication equipment [terminal]
- --- Test and measurement equipment
- --- Industrial control
- --- Audio visual equipment
- --- Consumer electronics

(ii) Measures such as fail-safe function and redundant design should be taken to ensure reliability and safety when SHARP devices are used for or in connection with equipment that requires higher reliability such as:

- --- Transportation control and safety equipment (i.e., aircraft, trains, automobiles, etc.)
- --- Traffic signals
- --- Gas leakage sensor breakers
- --- Alarm equipment
- --- Various safety devices, etc.

(iii) SHARP devices shall not be used for or in connection with equipment that requires an extremely high level of reliability and safety such as:

- --- Space applications
- --- Telecommunication equipment [trunk lines]
- --- Nuclear power control equipment
- --- Medical and other life support equipment (e.g., scuba).

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